

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S31	85	semiconductor and ((silicon adj oxide) same beam same remov\$3 same irradiat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:49
L1	118	semiconductor and ((silicon adj oxide) same beam same remov\$3 same irradiat\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 15:49
S18	65	semiconductor and (energy or particle) and oxygen adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 16:37
L2	130	semiconductor and (energy or particle) and oxygen adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 16:37
S4	3	S3 and (cobalt near2 (disilicide or silicide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 16:46
L3	334	(shin near2 hashimoto or takenobu near2 kishida or kyoko near2 egashira or yoshifumi near2 hata or toru near2 nishiwaki or tomoya near2 tanaka).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 16:46
S2	11	anneal\$5 near10 laser near10 ion near2 beam near5 (ar or argon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 16:47
L5	13	anneal\$5 near10 laser near10 ion near2 beam near5 (ar or argon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 16:47
L4	3	L3 and (cobalt near2 (disilicide or silicide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 16:47
L6	61	(silicon near2 (oxide or dioxide) or (sio or "sio.sub.2")) near10 (argon or ar) near5 beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 16:51

S51	54	("cosi.sub.2" or (cobalt adj (disilicide or silicide))) and semiconductor and "silicon oxide" and (oxygen same concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 17:28
S17	65	semiconductor and ((energy or particle) adj beam same (silicon adj oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 17:28
L8	194	("cosi.sub.2" or (cobalt adj (disilicide or silicide))) and semiconductor and "silicon oxide" and (oxygen same concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 17:28
L7	115	semiconductor and ((energy or particle) adj beam same (silicon adj oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 17:28
S10 0	52	(silicon near2 (oxide or dioxide) or (sio or "sio.sub.2")) near10 (argon or ar) near5 beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 17:29
L9	61	(silicon near2 (oxide or dioxide) or (sio or "sio.sub.2")) near10 (argon or ar) near5 beam	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 17:29